

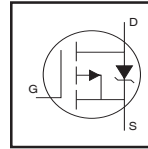
Features

- Advanced Planar Technology
- P-Channel MOSFET
- Low On-Resistance
- Dynamic dV/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to T_{jmax}
- Lead-Free, RoHS Compliant
- Automotive Qualified *

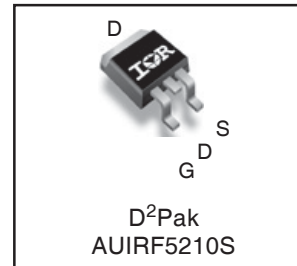
Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

HEXFET® Power MOSFET



$V_{(BR)DSS}$	-100V
$R_{DS(on)}$ max.	60mΩ
I_D	-38A



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V	-38	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V	-24	
I_{DM}	Pulsed Drain Current ①	-140	
P_D @ $T_A = 25^\circ\text{C}$	Maximum Power Dissipation	3.1	W
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	170	
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	120	mJ
I_{AR}	Avalanche Current ①	-23	A
E_{AR}	Repetitive Avalanche Energy ①	17	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-7.4	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state) ⑤	—	40	

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*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-100	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.11	—	V/°C	Reference to 25°C , $I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	60	m Ω	$V_{GS} = 10V, I_D = -38A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$V_{GS(th)}$	Forward Transconductance	9.5	—	—	S	$V_{DS} = -50V, I_D = -23A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-50	μA	$V_{DS} = -100V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	150	230	nC	$I_D = -23A$
Q_{gs}	Gate-to-Source Charge	—	22	33		$V_{DS} = -80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	81	120		$V_{GS} = -10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = -50V$
t_r	Rise Time	—	63	—		$I_D = -23A$
$t_{d(off)}$	Turn-Off Delay Time	—	72	—		$R_G = 2.4\Omega$
t_f	Fall Time	—	55	—		$V_{GS} = -10V$ ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	2780	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	800	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	430	—		$f = 1.0MHz$, See Fig. 5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-38	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-140		
V_{SD}	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -23A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	170	260	ns	$T_J = 25^\circ\text{C}, I_F = -23A, V_{DD} = -25V$
Q_{rr}	Reverse Recovery Charge	—	1180	1770	nC	$di/dt = -100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.46mH$
 $R_G = 25\Omega$, $I_{AS} = -23A$. (See Figure 12)
- ③ $I_{SD} \leq -23A$, $di/dt \leq -650A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.

- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑥ R_{θ} is measured at T_J approximately 90°C

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D ² Pak	MSL1
ESD	Machine Model	Class M4 (+/- 425V) ^{††} AEC-Q101-002	
	Human Body Model	Class H2 (+/- 4000V) ^{††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1125V) ^{††} AEC-Q101-005	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

^{††} Highest passing voltage.

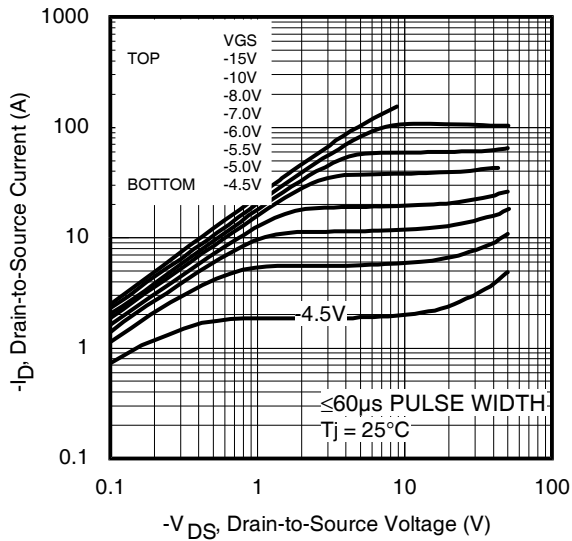


Fig 1. Typical Output Characteristics

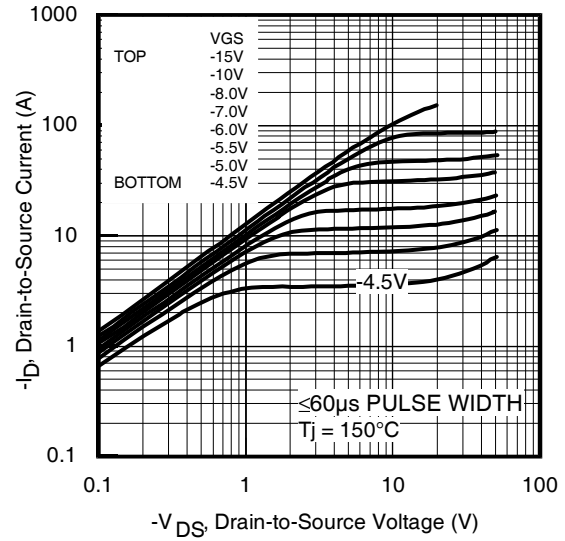


Fig 2. Typical Output Characteristics

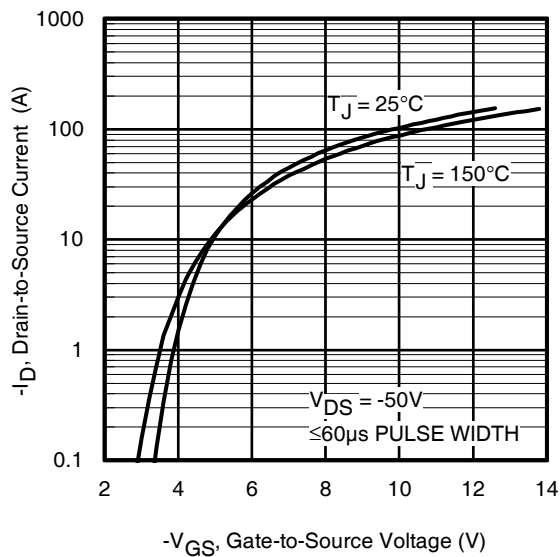


Fig 3. Typical Transfer Characteristics

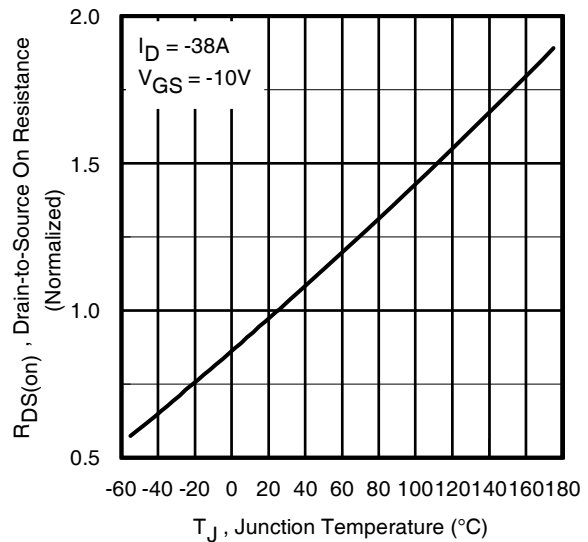


Fig 4. Normalized On-Resistance
vs. Temperature

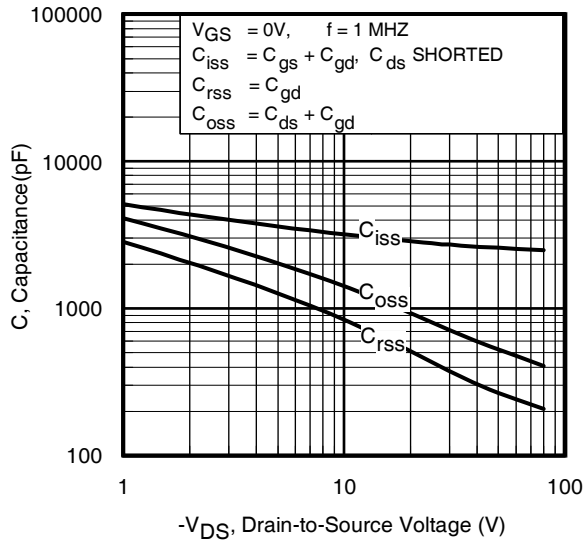


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

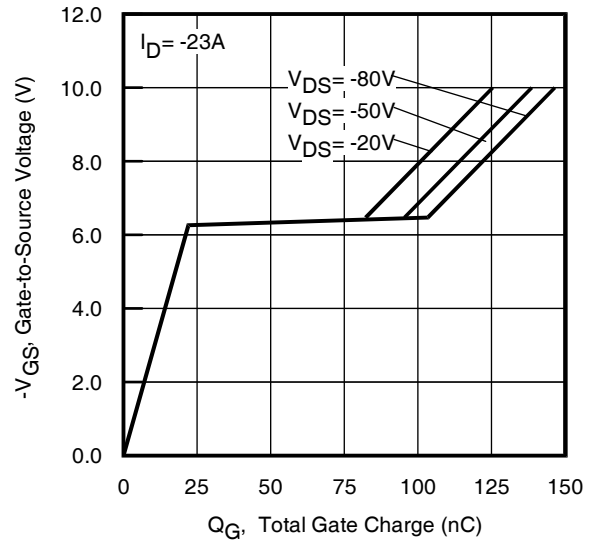


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

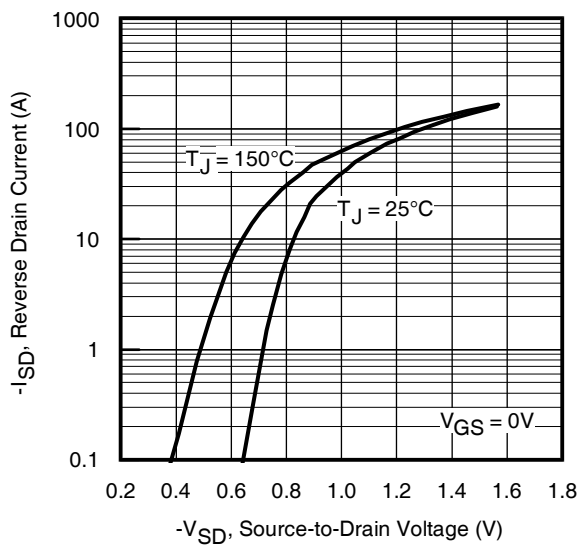


Fig 7. Typical Source-Drain Diode Forward Voltage

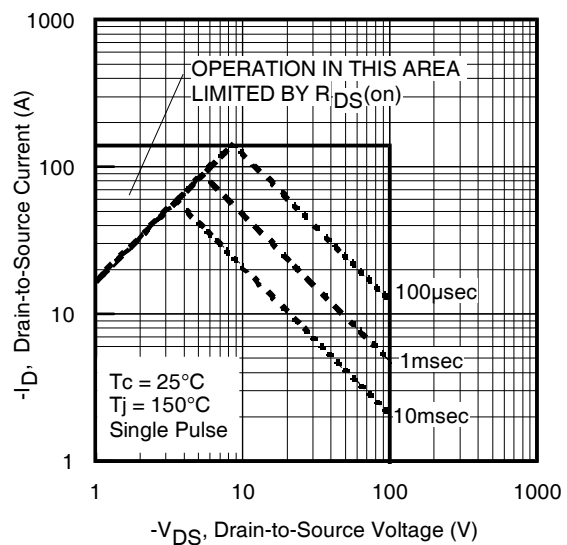


Fig 8. Maximum Safe Operating Area

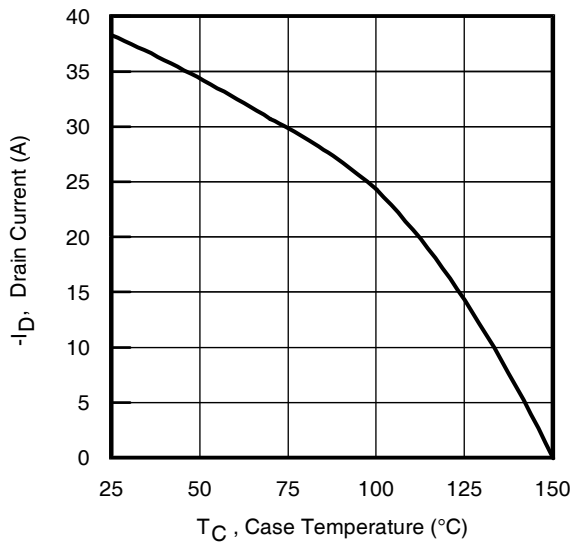


Fig 9. Maximum Drain Current vs. Case Temperature

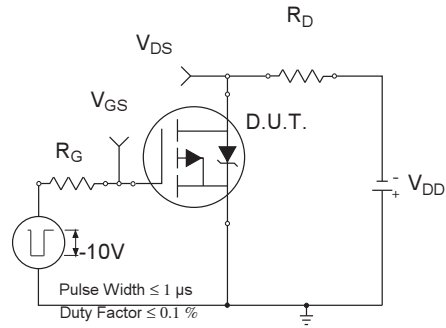


Fig 10a. Switching Time Test Circuit

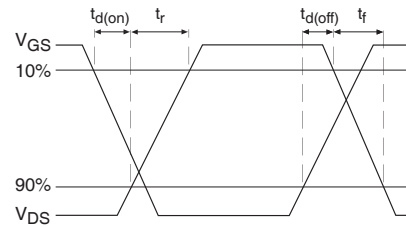


Fig 10b. Switching Time Waveforms

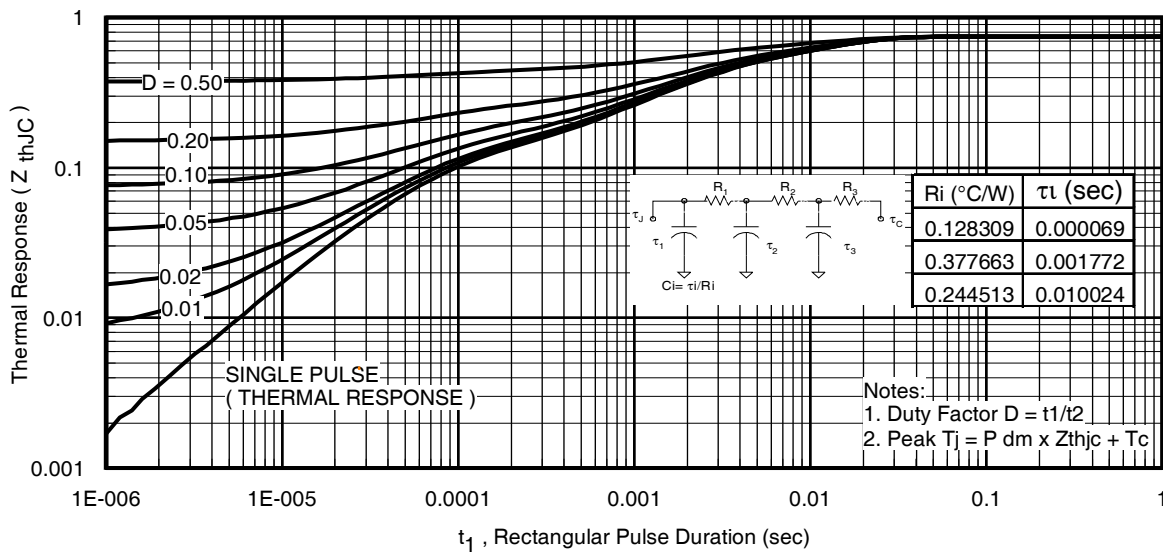


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

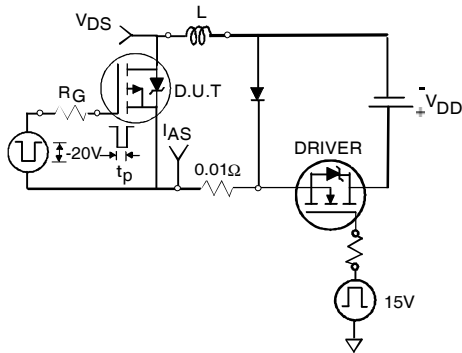


Fig 12a. Unclamped Inductive Test Circuit

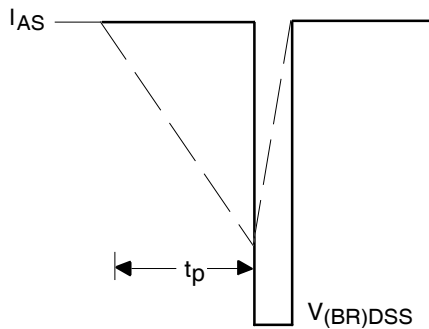


Fig 12b. Unclamped Inductive Waveforms

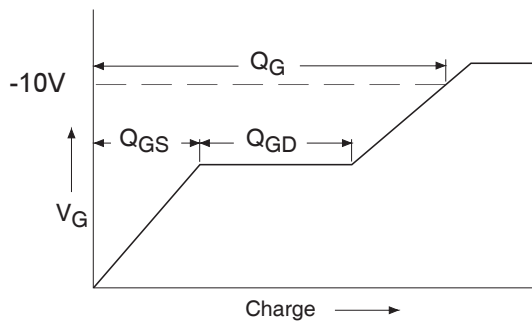


Fig 14a. Basic Gate Charge Waveform

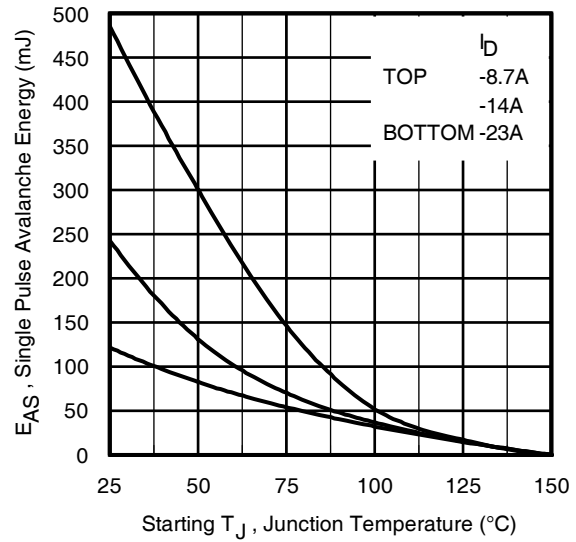


Fig 13. Maximum Avalanche Energy vs. Drain Current

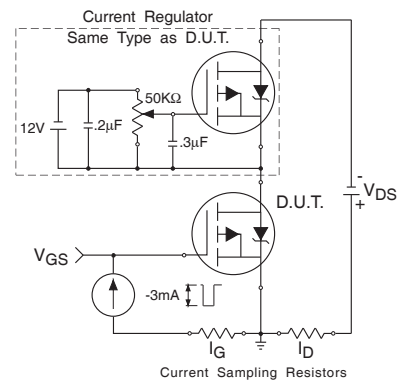
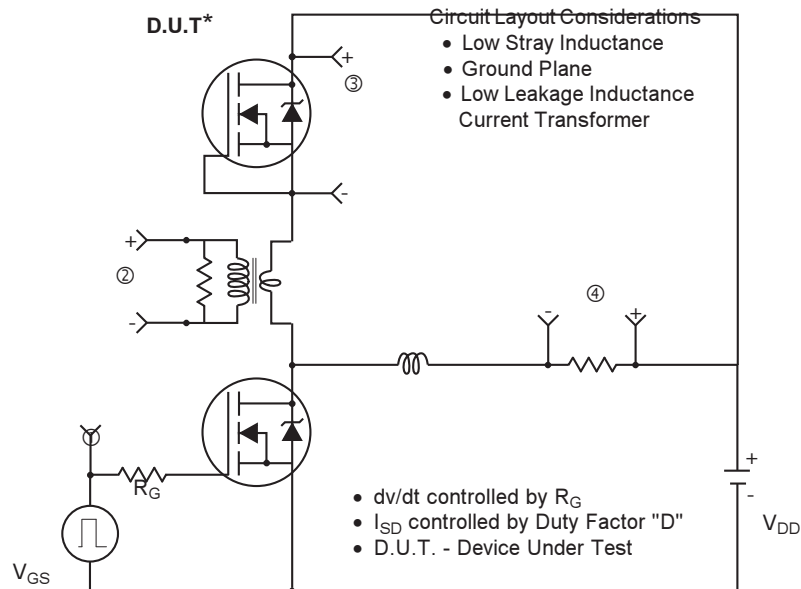
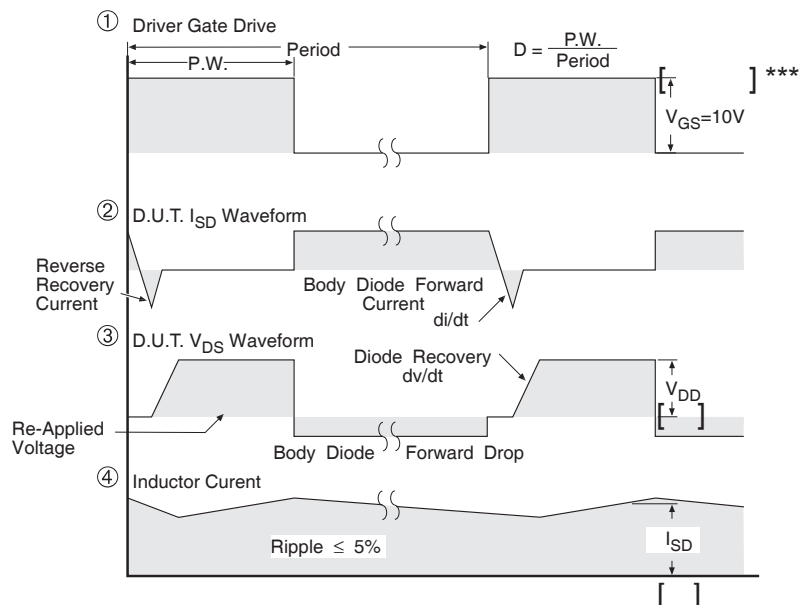


Fig 14b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel

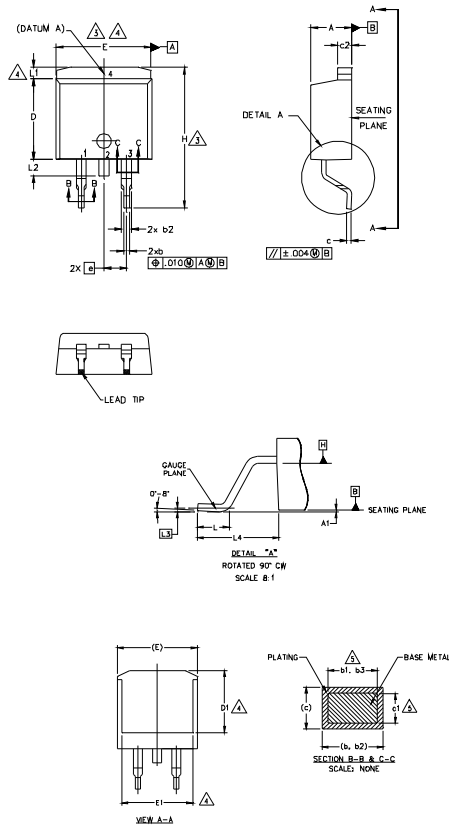


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 15. For P-Channel HEXFETS

D²Pak Package Outline

(Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b1	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	2.54	BSC	.100	BSC	
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	—	1.65	—	.066	4
L2	1.27	1.78	—	.070	
L3	0.25	BSC	.010	BSC	
L4	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

HEXFET

1. — GATE
- 2, 4. — DRAIN
3. — SOURCE

IGBTs, CoPACK

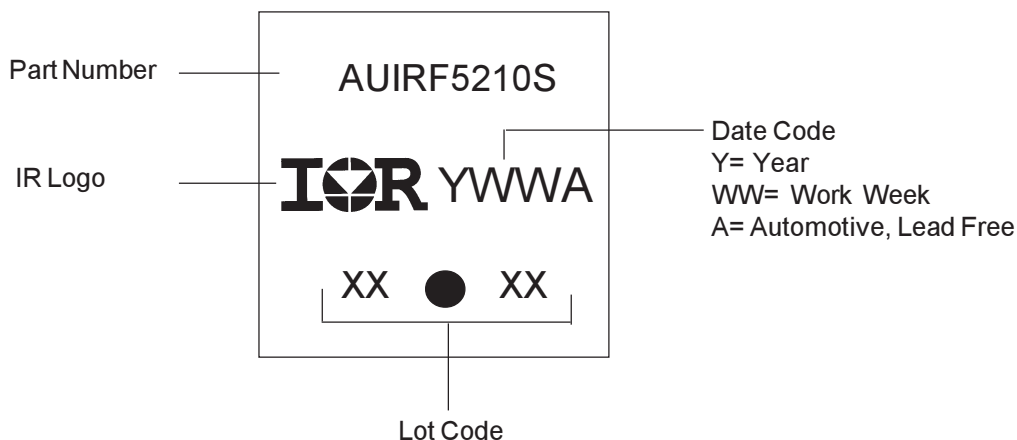
1. — GATE
- 2, 4. — COLLECTOR
3. — EMITTER

DIODES

1. — ANODE *
- 2, 4. — CATHODE
3. — ANODE

* PART DEPENDENT.

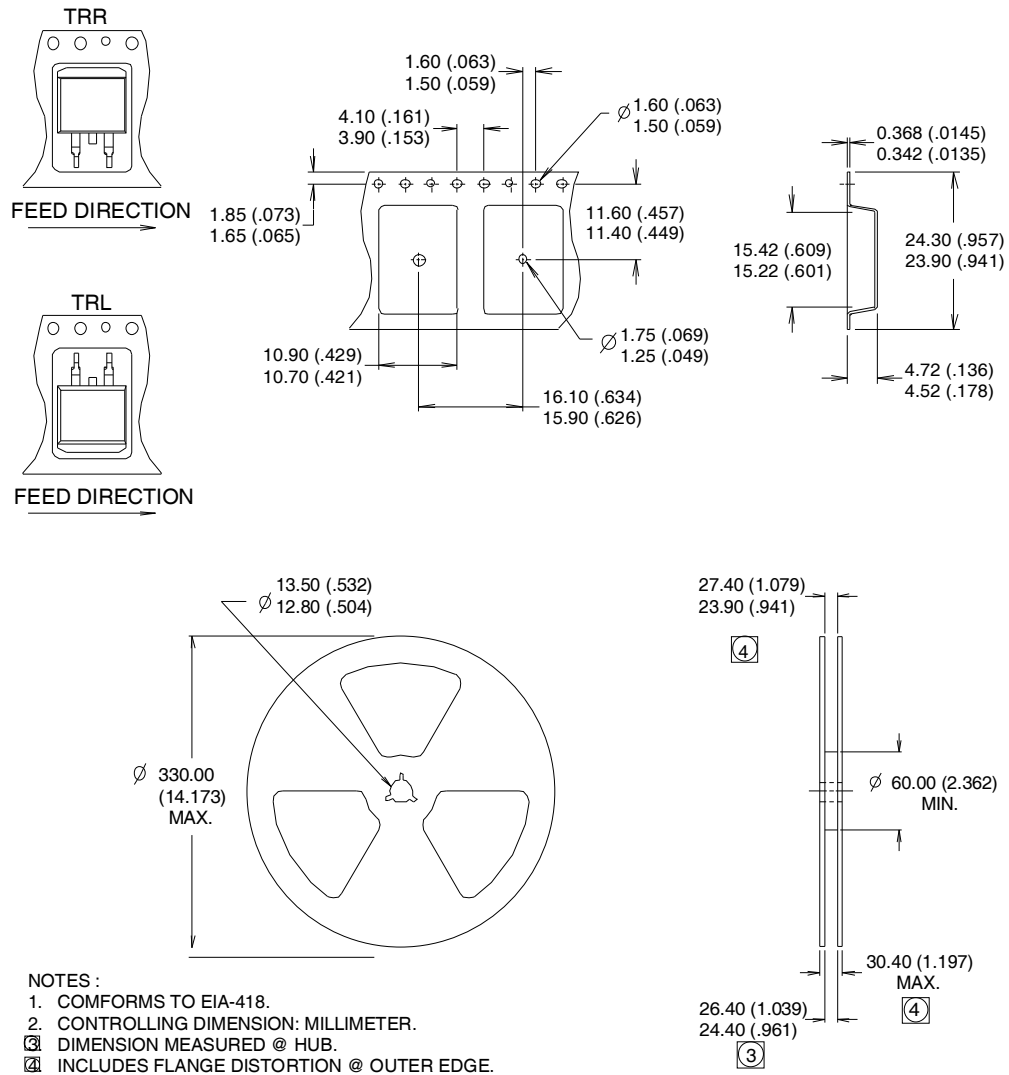
D²Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF5210S	D2Pak	Tube	50	AUIRF5210S
		Tape and Reel Left	800	AUIRF5210STRL
		Tape and Reel Right	800	AUIRF5210STRR

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